

Amendments to the Specification:

At page 1, following the title "Conductor Crossover for a Semiconductor Detector," and preceding the title "Background of the Invention," insert the following:

Cross Reference to Related Applications

This application is a National Stage application of international application No. PCT/EP03/03209 filed on March 27, 2003 in the European Receiving Office, priority from which is here claimed.

At page 7, rewrite the paragraph beginning at line 12 as follows:

Multiple annular semiconductor electrodes 2 are situation situated on the top side of the semiconductor substrate 1 which concentrically surround the readout electrode A. Each of the individual semiconductor electrodes 2 is composed of a p-doped semiconductor material, whereby the doping of the semiconductor electrodes 2 is so strong that total depletion does not occur during operation. The semiconductor electrodes are also referred to as field rings R₁ through R_n.